

Description

The LMTL1P10 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

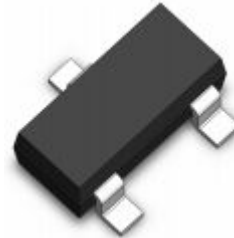
$V_{DS} = -100V$ $I_D = -0.9 A$

$R_{DS(ON)} < 0.65\Omega$ @ $V_{GS}=10V$

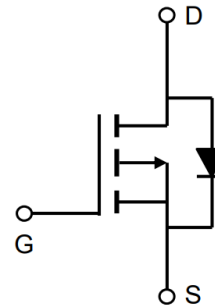
Application

- Battery protection
- Load switch
- Uninterruptible power supply

Dimensions SOT-23



Pin Configuration



Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LMTL1P10	0107	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-0.9	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-0.7	A
I_{DM}	Pulsed Drain Current ²	-1.8	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.0624	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-0.8A	---	0.52	0.65	Ω
		V _{GS} =-4.5V, I _D =-0.4A	---	0.56	0.7	
VGS(th)	Gate Threshold Voltage		-1.0	-1.5	-2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient	V _{GS} =V _{DS} , I _D =-250uA	---	4.5	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-80V, V _{GS} =0V, T _J =25°C	---	---	10	uA
		V _{DS} =-80V, V _{GS} =0V, T _J =55°C	---	---	100	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-5V, I _D =-0.8A	---	3	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	16	32	Ω
Q _g	Total Gate Charge (-4.5V)		---	4.5	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-0.5A	---	1.14	---	
Q _{gd}	Gate-Drain Charge		---	1.5	---	
T _{d(on)}	Turn-On Delay Time		---	13.6	---	ns
T _r	Rise Time	V _{DD} =-50V, V _{GS} =-10V, R _G =3.3Ω	---	6.8	---	
T _{d(off)}	Turn-Off Delay Time	I _D =-0.5A	---	34	---	
T _f	Fall Time		---	3	---	
C _{iss}	Input Capacitance		---	553	---	pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	29	---	
C _{rss}	Reverse Transfer Capacitance		---	20	---	
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-0.9	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-1.8	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

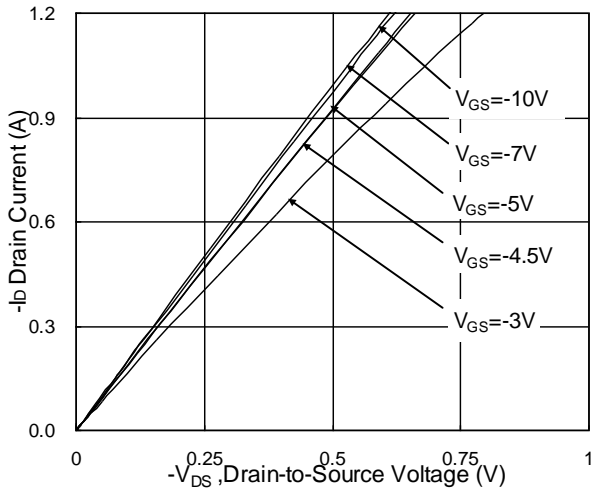


Fig.1 Typical Output Characteristics

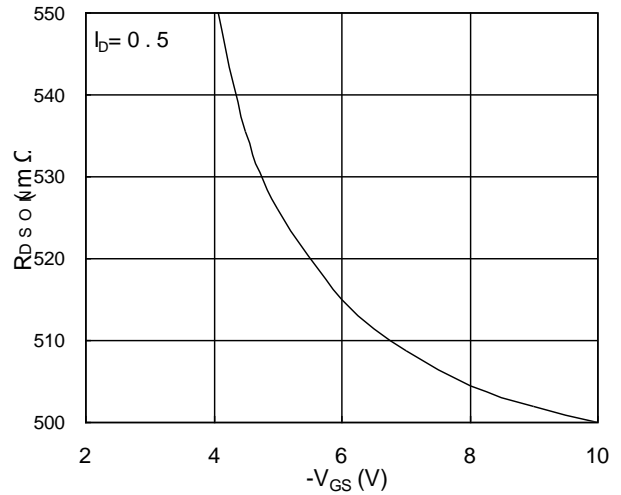


Fig.2 On-Resistance vs. Gate-Source

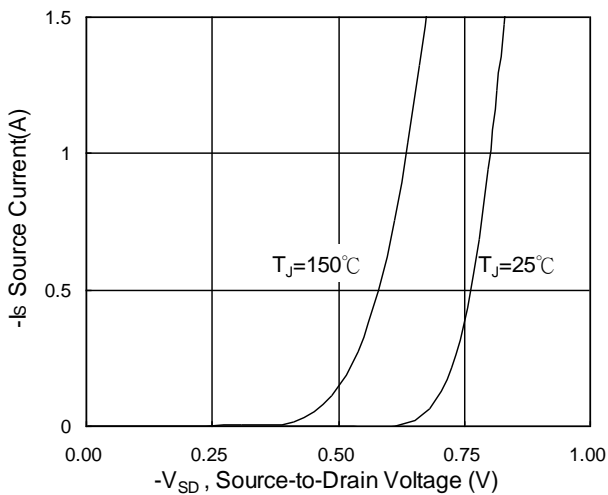


Fig.3 Forward Characteristics Of Reverse

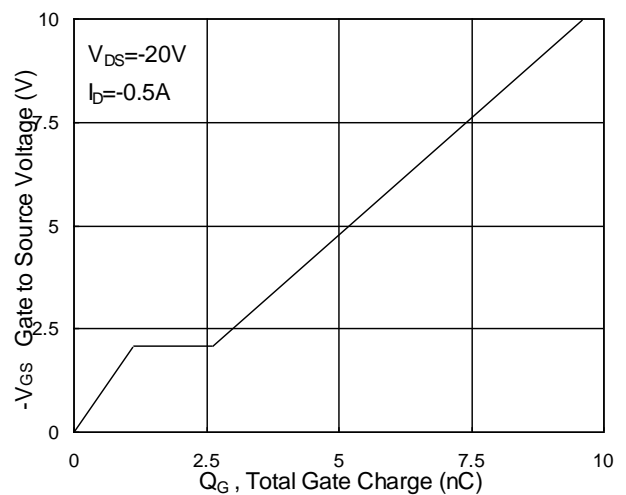


Fig.4 Gate-Charge Characteristics

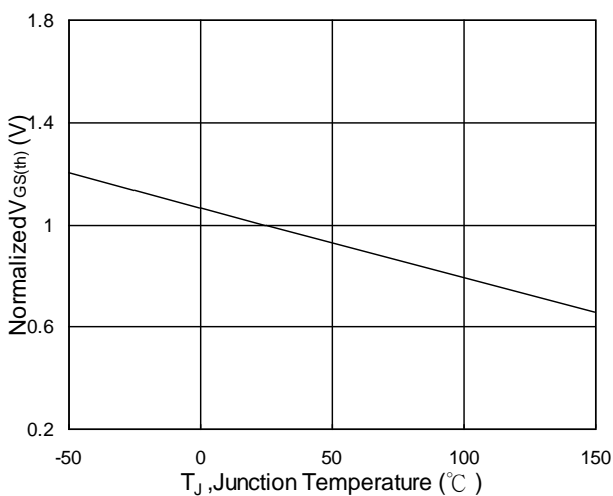


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

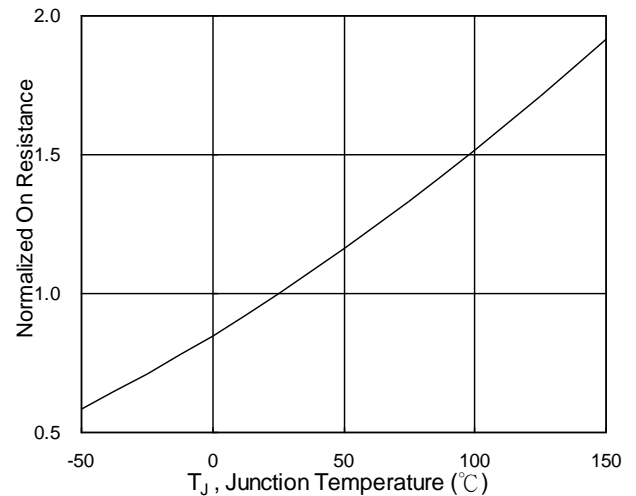


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

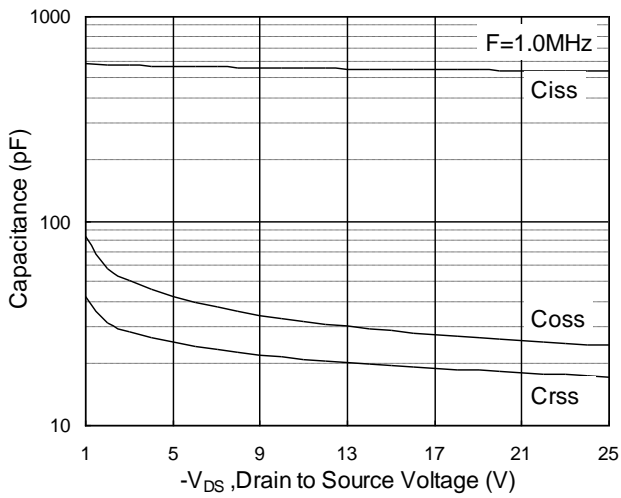


Fig.7 Capacitance

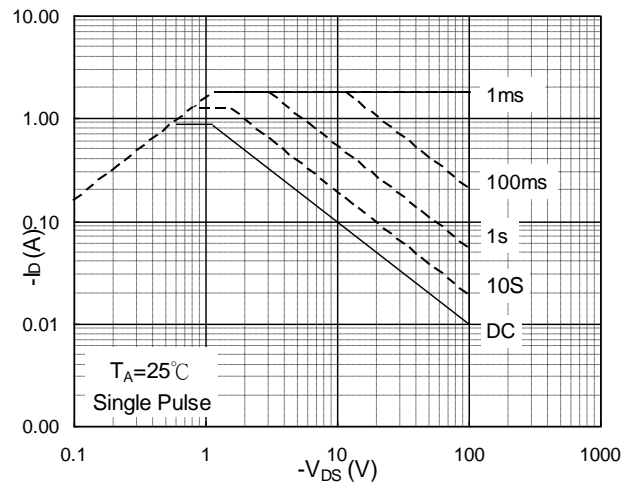


Fig.8 Safe Operating Area

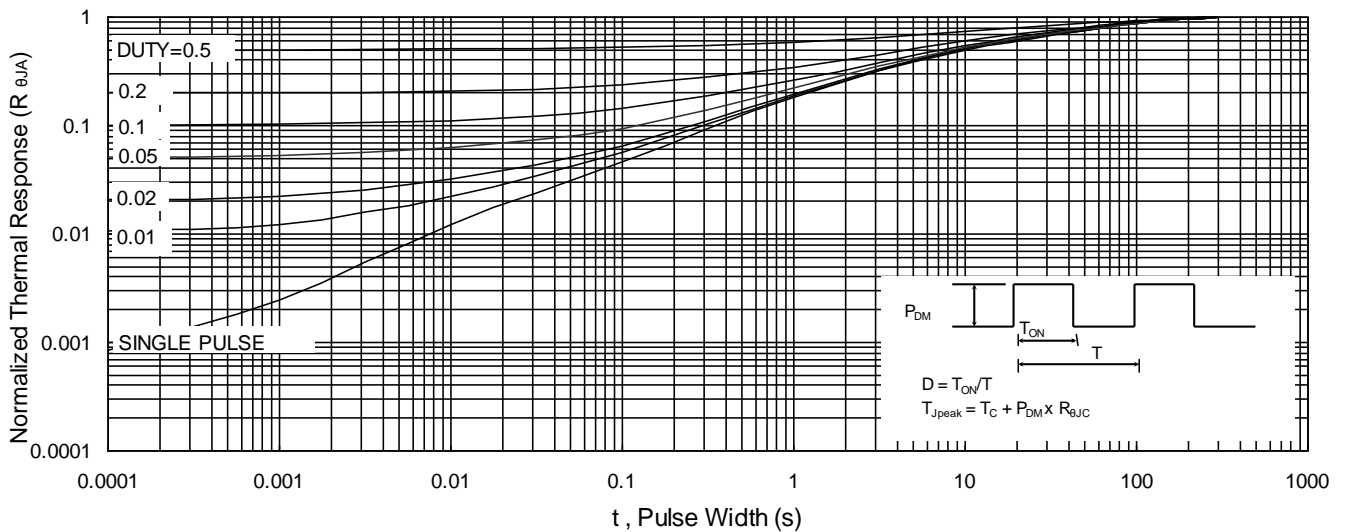


Fig.9 Normalized Maximum Transient Thermal Impedance

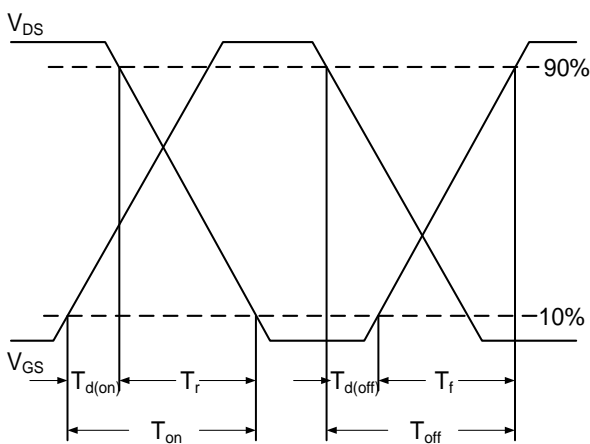


Fig.10 Switching Time Waveform

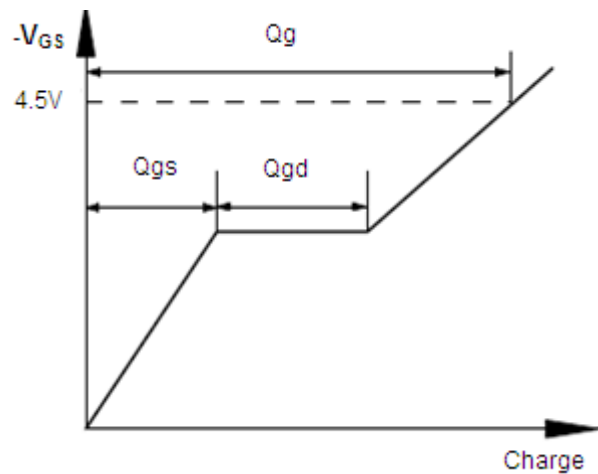
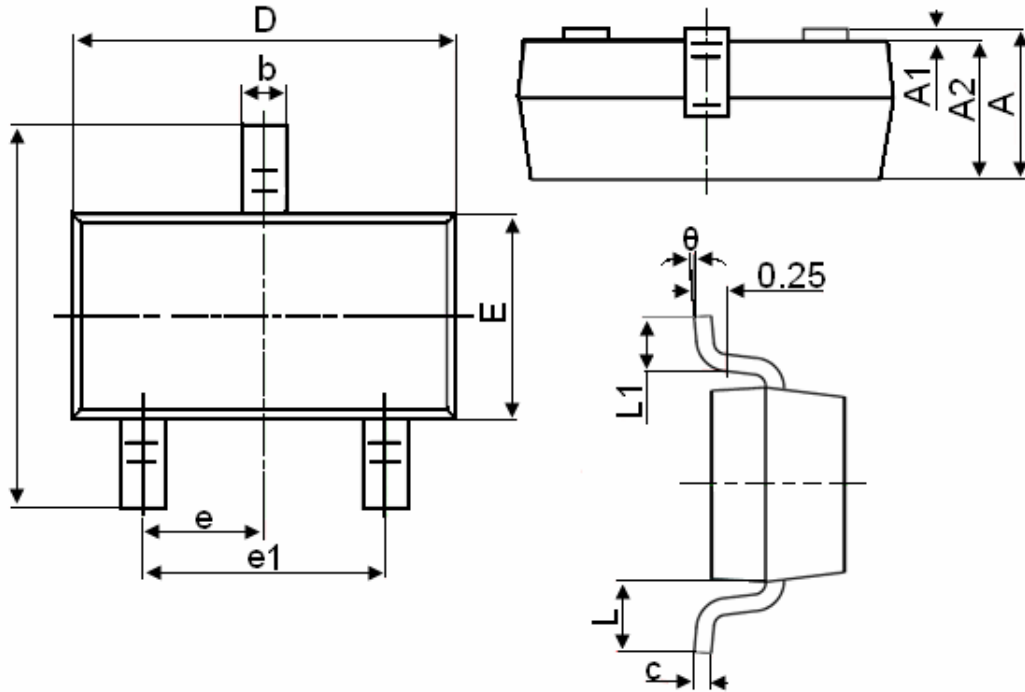


Fig.11 Gate Charge Waveform

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°